

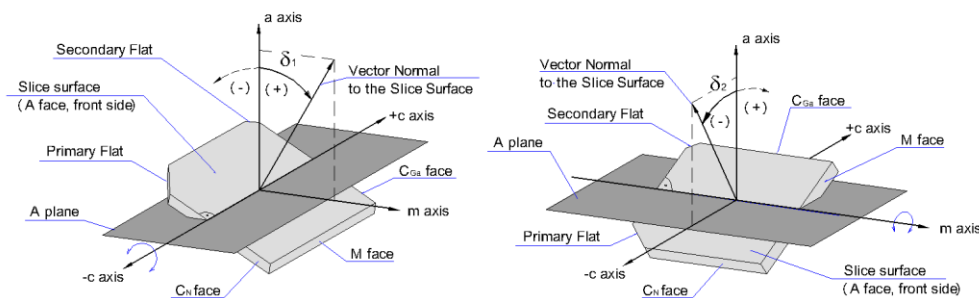
HIGH ELECTRON CONCENTRATION WAFERS

n-type

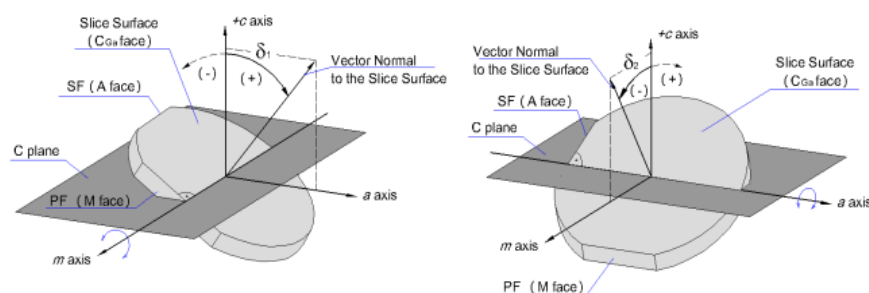
The substrate is sliced from a mono-crystalline bulk material grown by ammonothermal method.

TECHNICAL SPECIFICATION				
Features	Units	Available planes		
		c-plane (0001)	m-plane (10 $\bar{1}0$)	Semipolar (20 $\bar{2}1$)
Carrier concentration	cm ⁻³	~10 ¹⁹		
Dopant		Oxygen-doped		
Resistivity	Ωcm	~ 10 ⁻³		
Mobility	cm ² /Vs	~ 150		
Thickness	μm	300-400		
Total thickness variation (TTV)	μm	≤40	≤20	≤20
Bow	μm	≤10		
FWHM (0002) of X-ray rocking curve, epi-ready surface at 100 μm x 100 μm slit	arcsec	~20	~20	~20
Dislocation density (EPD)	cm ⁻²	< 5 x 10 ⁴		
Misorientation	deg	Od demand		
Surface finishing	Front side	Mechano-chemically polished (epi-ready RMS <0,5nm)		
	Back side	Lapped		
Available sizes		10x10 1-inch 1,5-inch 1,8-inch 2-inch	10x10 13x15	10x10 13x15
Available grades		Test grade Production grade Prime grade	Prime grade	Prime grade
Packaging		Separate single wafer container		
Special request		For pricing or technical enquiries please contact our sales team		

Square shape



Round shape



Note:

The information given above may be subject to change at any time without notice. This leaflet is not an offer within the meaning of sales or commercial law. The AMMONO-GaN substrates are offered for sale under Ammono's General Terms and Conditions.